

Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	To Be Assigned 10/826502
		Filing Date	Herewith
		First Named Inventor	Weiss et al.
		Art Unit	To Be Assigned
		Examiner Name	To Be Assigned
Sheet 1 of 3	Attorney Docket Number	176/61511 (2-11144-03043)	

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
JMB	1	US-5,651,818	07/29/1997	Milstein et al.	
JMB	2	US-5,682,401	10/28/1997	Joannopoulos et al.	
JMB	3	US-5,740,287	04/14/1998	Scalora et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup> Number <sup>3</sup> Kind Code <sup>2</sup> (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>4</sup>
JMB	4	Barla et al., "Determination of Lattice Parameter and Elastic Properties of Porous Silicon By X-Ray Diffraction," <i>Growth</i> 68:727-732 (1984)	
JMB	5	Birner et al., "Silicon-Based Photonic Crystals," <i>Adv. Mater.</i> 13:377-389 (2001)	
JMB	6	Striener et al., "Dynamic Etching of Silicon for Broadband Antireflection Applications," <i>Appl. Phys. Lett.</i> 81:2980-2982 (2002)	

Examiner Signature	<i>J. Martin Blin</i>	Date Considered	01/10/2006
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	7	Buttard et al., "X-Ray-Diffraction Investigation of the Anodic Oxidation of Porous Silicon", <i>J. Appl. Phys.</i> 79:8060-8070 (1996)	
	8	Buttard et al., "Porous Silicon Strain During in situ Ultrahigh Vacuum Thermal Annealing," <i>J. Appl. Phys.</i> 85:7105-7111 (1999)	
	9	Yablonovitch et al., "Inhibited Spontaneous Emission in Solid-State Physics and Electronics," <i>Phys. Rev. Lett.</i> 58:2059-2062 (1987)	
	10	Bai et al., "Strain in Porous Si Formed on a Si (100) Substrate," <i>Appl. Phys. Lett.</i> 57:2247-2249 (1990)	
	11	Jellison et al., "The Temperature Dependence of the Refractive Index of Silicon at Elevated Temperatures at Several Laser Wavelengths," <i>J. Appl. Phys.</i> 60:841-843 (1986)	
	12	Martinez, G., in <i>Handbook on Semiconductors Volume 2: Optical Properties of Solids</i> , M. Balkanski, ed. North-Holland Publishing Company, New York, NY, pp. 181-222 (1980)	
	13	Lopez et al., "Erbium Emission from Porous Silicon One-Dimensional Photonic Band Gap Structures," <i>Appl. Phys. Lett.</i> 77:3704-3706 (2000)	
	14	Sugiyama et al., "Microstructure and Lattice Distortion of Anodized Porous Silicon Layers," <i>J. Cryst. Growth</i> 103:156-163 (1990)	
	15	Kim et al., "Effective Method for Stress Reduction in Thick Porous Silicon Films," <i>Appl. Phys. Lett.</i> 80:2287-2289 (2002)	
	16	Lugo et al., "Porous Silicon Multilayer Structures: A Photonic Band Gap Analysis," <i>J. Appl. Phys.</i> 91:4966-4972 (2002)	
	17	Hirschman et al., "Silicon-Based Visible Light-Emitting Devices Integrated Into Microelectric Circuits," <i>Nature</i> 384:338-341 (1996)	
	18	Young et al., "X-Ray Double Crystal Diffraction Study of Porous Silicon," <i>Appl. Phys. Lett.</i> 46:1133-1135 (1985)	

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	19	Savage, N., "Linking with Light," <i>IEEE Spectrum</i> 39:32-36 (2002)	
	20	Painter et al., "Two-Dimensional Photonic Band-Gap Defect Mode Laser," <i>Science</i> 284:1819-1821 (1999)	
	21	Reece et al., "Optical Microactivities with Subnanometer Linewidths Based on Porous Silicon," <i>Appl. Phys. Lett.</i> 81:4895-4897 (2002)	
	22	Lee et al., "Operation of Photonic Crystal Membrane Lasers Above Room Temperature," <i>Appl. Phys. Lett.</i> 81:3311-3313 (2002)	
	23	John, S., "Strong Localization of Photons in Certain Disordered Dielectric Superlattices," <i>Phys. Rev. Lett.</i> 58:2486-2489 (1987)	
	24	Weiss et al., "Electrically Tunable Silicon-Based Mirrors," <i>Proc. of SPIE</i> 4654:36-44 (2002)	
	25	Lin et al., "Demonstration of Highly Efficient Waveguiding in a Photonic Crystal Slab at the 1.5- $\mu$ m Wavelength," <i>Opt. Lett.</i> 25:1297-1299 (2000)	
	26	Theiß, W., "Optical Properties of Porous Silicon," <i>Surf. Sci. Rep.</i> 29:91-192 (1997)	
	27	Zhou et al., "The Effect of Thermal Processing on Multilayer Porous Silicon Microactivity," <i>Phys. Stat. Sol. A</i> 182:319-324 (2000)	
	28	Weiss et al., "Temperature Stability for Silicon-Based Photonic Band-Gap Structures," <i>Applied Physics Letters</i> 83:1980-1982 (2003)	
	29	DeLouise, Lisa, [http://www.futurehealth.rochester.edu/miller_group/people/lisa_delouise.html] Miller Research Group pp. 1-4 (2004)	
	30	S.M. Weiss, "Control of One-Dimensional Photonic Bandgap Thermal Tuning," <i>Phys. Stat. Sol.</i> pp. 1-5 (Unpublished)	
	31	Grayson, M., ed., <i>Encyclopedia of Semiconductor Technology</i> , John Wiley and Sons, New York, pp. 374 (1984)	

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